

Dual N-Channel Power MOSFET

40V, 48A, 11mΩ

FEATURES

- Low R_{DS(ON)} to minimize conductive losses
- Low gate charge for fast power switching
- 100% UIS and R_a tested
- RoHS Compliant
- Halogen-free according to IEC 61249-2-21

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- BLDC Motor Control
- Battery Power Management
- DC-DC Converter
- Secondary Synchronous Rectification

KEY PERFORMANCE PARAMETERS				
PARAMETER		VALUE	UNIT	
V_{DS}		40	V	
R _{DS(on)} (max)	$V_{GS} = 10V$	11	mΩ	
	$V_{GS} = 7V$	17.2		
Q_g		25	nC	



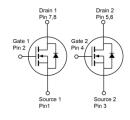




PDFN56 Dual







Note: MSL 1 (Moisture Sensitivity Level) per J-STD-020

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	40	V	
Gate-Source Voltage		V_{GS}	±20	V	
Continuous Drain Current (Note 1)	$T_C = 25^{\circ}C$		48	А	
Continuous Drain Current	$T_{C} = 25^{\circ}C$ $T_{A} = 25^{\circ}C$	I _D	10		
Pulsed Drain Current		I _{DM}	192	А	
Single Pulse Avalanche Current (Note 2)		I _{AS}	17	Α	
Single Pulse Avalanche Energy (Note 2)		E _{AS}	43	mJ	
Total Dayyar Dissination	$T_C = 25^{\circ}C$	Ь	48	W	
Total Power Dissipation	$T_C = 25^{\circ}C$ $T_C = 125^{\circ}C$	P _D	9.6		
Total Dayyar Dissination	$T_A = 25$ °C	2		14/	
Total Power Dissipation	T _A = 125°C	P _D	0.4	W	
Operating Junction and Storage Temperature Range		T _J , T _{STG}	- 55 to +150	°C	

THERMAL PERFORMANCE					
PARAMETER	SYMBOL	MAXIMUM	UNIT		
Junction to Case Thermal Resistance	R _{eJC}	2.6	°C/W		
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	61	°C/W		

Thermal Performance Note: $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistances. The case-thermal reference is defined at the solder mounting surface of the drain pins. $R_{\Theta JC}$ is guaranteed by design while $R_{\Theta CA}$ is determined by the user's board design. The $R_{\Theta JA}$ limit presented here is based on mounting on a 1 in² pad of 2 oz copper.



ELECTRICAL SPECIFICATIONS (T _A = 25°C unless otherwise noted)						
PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static						
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250\mu A$	BV _{DSS}	40			V
Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	$V_{GS(TH)}$	2	2.9	4	V
Gate-Source Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	I _{GSS}			±100	nA
	$V_{GS} = 0V, V_{DS} = 40V$				1	μA
Drain-Source Leakage Current	$V_{GS} = 0V, V_{DS} = 40V$ $T_{J} = 125^{\circ}C$	I _{DSS}			100	
Drain-Source On-State Resistance	$V_{GS} = 10V, I_D = 10A$			8.5	11	mΩ
(Note 3)	$V_{GS} = 7V$, $I_D = 8A$	R _{DS(on)}		10	17.2	
Forward Transconductance (Note 3)	$V_{DS} = 10V, I_{D} = 10A$	9 _{fs}		40		S
Dynamic (Note 4)						
Total Gate Charge	$V_{GS} = 10V, V_{DS} = 20V,$ $I_{D} = 10A$	Q_g		25		
Total Gate Charge	$V_{GS} = 7V, V_{DS} = 20V,$	Q_g		17		nC
Gate-Source Charge		Q_{gs}		7		
Gate-Drain Charge	$I_D = 8A$	Q_{gd}		6		
Input Capacitance	$V_{GS} = 0V, V_{DS} = 20V$ f = 1.0MHz	C _{iss}		1506		
Output Capacitance		C _{oss}		144		pF
Reverse Transfer Capacitance		C _{rss}		75		
Gate Resistance	f = 1.0MHz	R_g	0.6	1.9	3.8	Ω
Switching (Note 4)						
Turn-On Delay Time		t _{d(on)}		7		
Turn-On Rise Time	$V_{GS} = 10V, V_{DS} = 20V,$ $I_{D} = 10A, R_{G} = 2\Omega,$	t _r		10		
Turn-Off Delay Time		t _{d(off)}		15		ns
Turn-Off Fall Time		t _f		5		
Source-Drain Diode						•
Forward Voltage (Note 3)	$V_{GS} = 0V, I_{S} = 10A$	V_{SD}			1.2	V
Reverse Recovery Time	I _S = 10A ,	t _{rr}		15		ns
Reverse Recovery Charge	dl/dt = 100A/µs	Q_{rr}		8		nC

Notes:

- 1. Silicon limited current only.
- 2. L = 0.3mH, $V_{GS} = 10$ V, $V_{DD} = 25$ V, $R_G = 25\Omega$, $I_{AS} = 17$ A, Starting $T_J = 25$ °C
- 3. Pulse test: Pulse Width \leq 300 μ s, duty cycle \leq 2%.
- 4. Switching time is essentially independent of operating temperature.

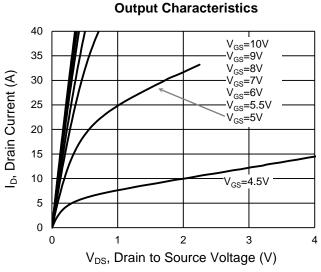
ORDERING INFORMATION

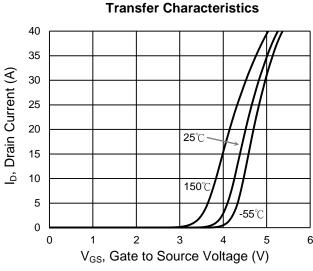
ORDERING CODE	PACKAGE	PACKING
TSM110NB04DCR RLG	PDFN56 Dual	2,500pcs / 13" Reel

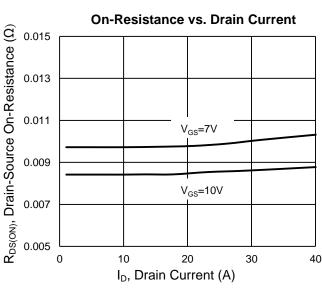


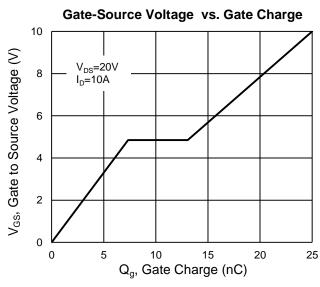
CHARACTERISTICS CURVES

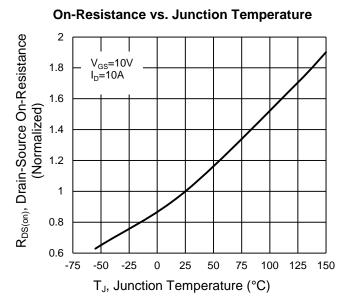
 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

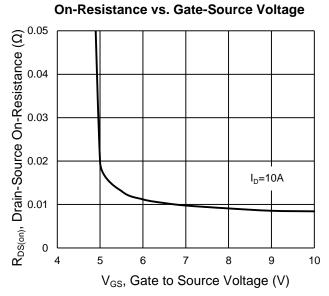










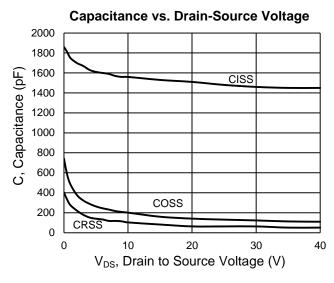


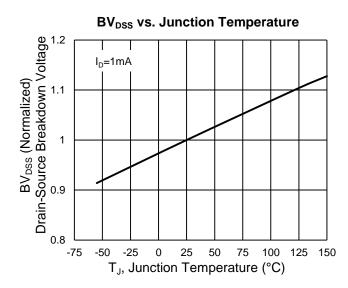
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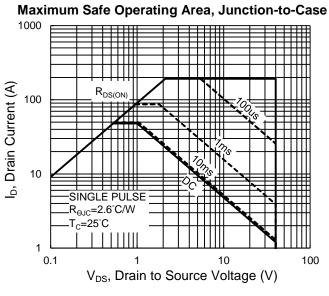


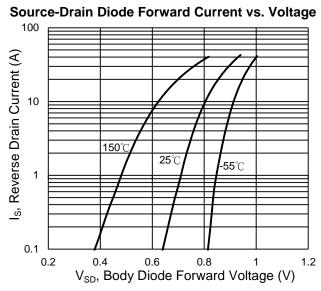
CHARACTERISTICS CURVES

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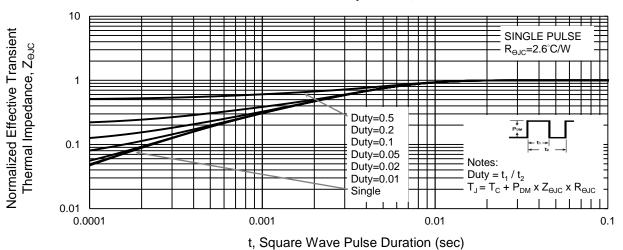




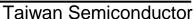








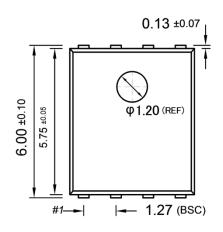
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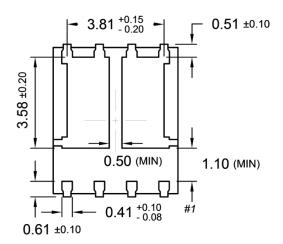


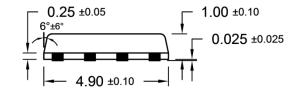


PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)

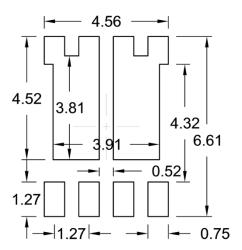
PDFN56 Dual







SUGGESTED PAD LAYOUT (Unit: Millimeters)



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MARKING DIAGRAM



Y = Year Code

WW = Week Code (01~52)

L = Lot Code (1~9,A~Z)

F = Factory Code



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